holes 12 formed on either edge of the above mentioned insulation film, and through holes 14 are disposed two-dimensionally between the rows of sprocket holes 12. Pitch *p* between through holes 14 is determined by the relationship *m p = n L (i.e., n* and m are integers, and *n<m),* wherein pitch of the sprocket holes is taken to be *L*. Through holes 14 are selectively utilized during formation of the desired circuit pattern upon insulation film 10 according to size of the manufactured semiconductor package. --

In the Claims:

Please cancel claims 5-11.

Please amend claims 1-4 as follows:

1. (amended) An insulation film for providing an insulation substrate for carrying a semiconductor chip of a semiconductor package comprising:

two rows of sprocket holes comprising a plurality of sprocket holes formed at a pitch L along both edges of the insulation film;

a plurality of through holes is formed two-dimensionally at a pitch p between the rows of sprocket holes; and

the plurality of through holes for use selectively as through holes for the insulation substrate of the semiconductor package according to size of the semiconductor package.

2. (amended) The insulation film according to claim 1 wherein the pitch L and the pitch p satisfy the following equation: m p = n L wherein n and m are integers that satisfy the equation n < m.